Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

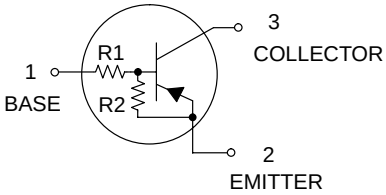
LDTA123EWT1G

- **Applications**
  Inverter, Interface, Driver

- **Features**
  1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
  2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
  3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

SOT–323 (SC–70)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V_{CC}	–50	V
Input voltage	V_{IN}	–12 to +10	V
Output current	I_O	–100	mA
	$I_{C(Max.)}$	–100	mA
Power dissipation	P_D	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTA123EWT1G	6H	2.2	2.2	3000/Tape & Reel
LDTA123EWT3G	6H	2.2	2.2	10000/Tape & Reel

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	–	–	–0.5	V	V_{CC}=–5V, I_O=–100μA
	$V_{I(on)}$	–3	–	–		V_O=–0.3V, I_O=–20mA
Output voltage	$V_{O(on)}$	–	–0.1	–0.3	V	I_O/I_I=–10mA/–0.5mA
Input current	I_I	–	–	–3.8	mA	V_I=–5V
Output current	$I_{O(off)}$	–	–	–0.5	μA	V_{CC}=–50V, V_I=0V
DC current gain	G_I	20	–	–	–	V_O=–5V, I_O=–20mA
Input resistance	R_1	1.54	2.2	2.86	kΩ	–
Resistance ratio	R_2/R_1	0.8	1	1.2	–	–
Transition frequency	f_T *	–	250	–	MHz	V_{CE}=–10V, I_E=5mA, f=100MHz

* Characteristics of built-in transistor

●Electrical characteristic curves

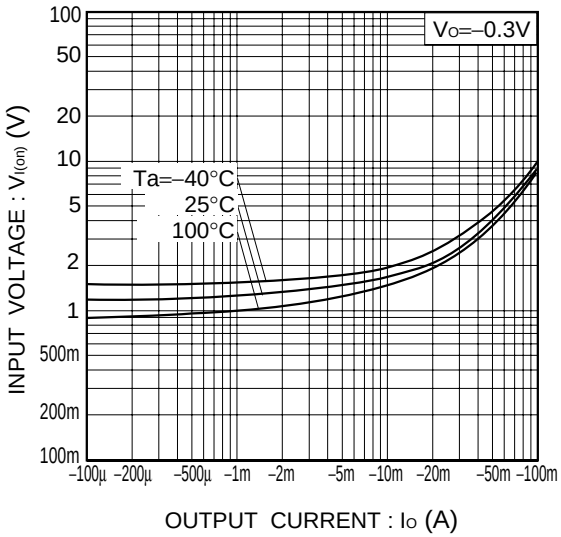


Fig.1 Input voltage vs. output current (ON characteristics)

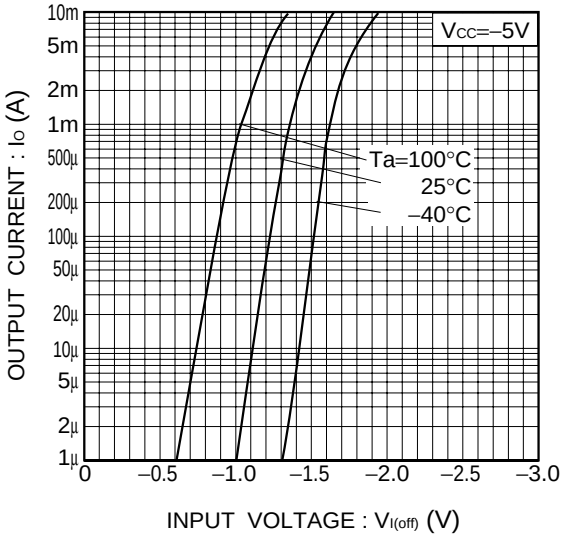


Fig.2 Output current vs. input voltage (OFF characteristics)

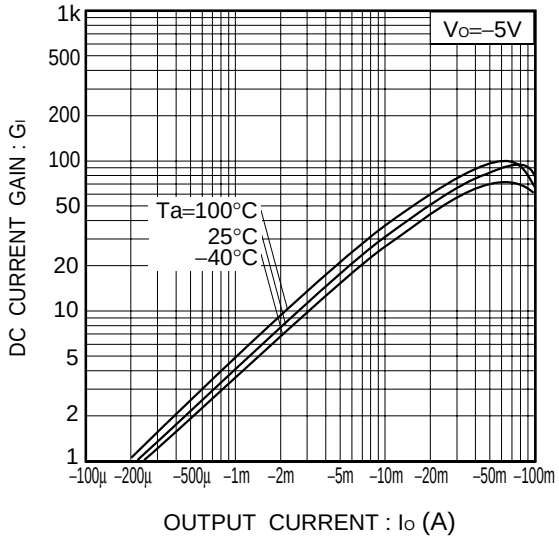


Fig.3 DC current gain vs. output current

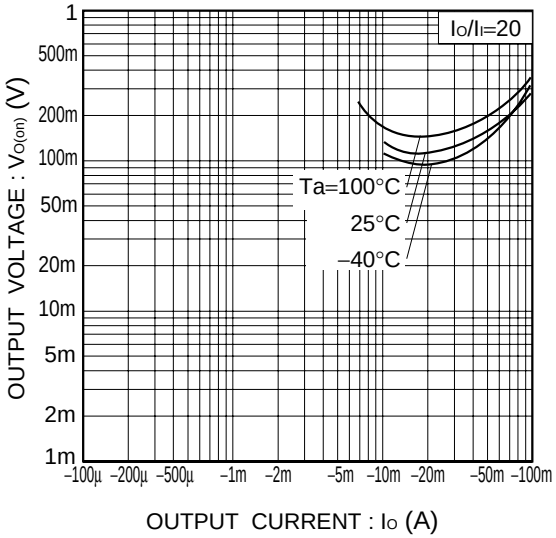
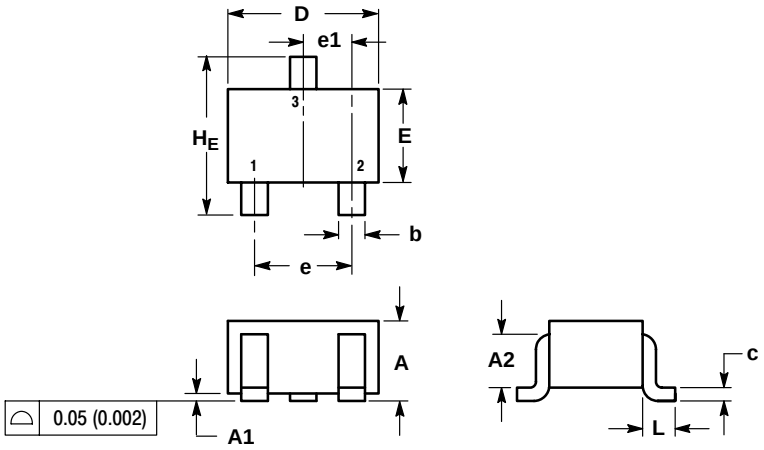


Fig.4 Output voltage vs. output current

LDTA123EWT1G

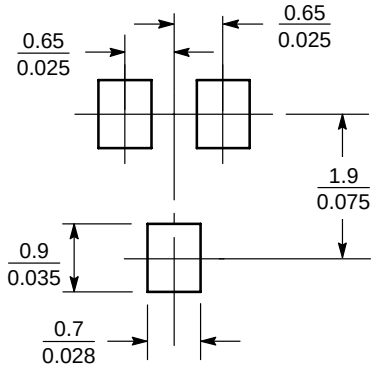
SC−70 (SOT−323)



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

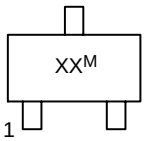
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.7 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L		0.425 REF			0.017 REF	
H_E	2.00	2.10	2.40	0.079	0.083	0.095

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{mm}{inches}\right)$

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.